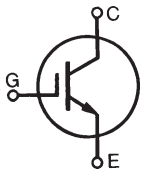
IXYS

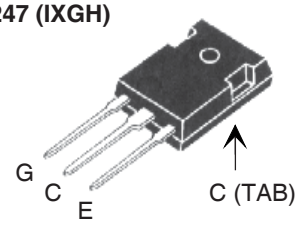
High Voltage IGBT

IXGH10N170
IXGT10N170

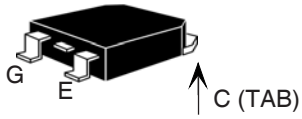
V_{CES} = 1700V
I_{C90} = 10A
$V_{CE(sat)} \leq$ 4.0V



TO-247 (IXGH)



TO-268 (IXGT)



G = Gate C = Collector
E = Emitter TAB = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_C = 25°C to 150°C	1700	V
V_{CGR}	T_J = 25°C to 150°C, R_{GE} = 1MΩ	1700	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	T_C = 25°C	20	A
I_{C90}	T_C = 90°C	10	A
I_{CM}	T_C = 25°C, 1ms	70	A
SSOA	V_{GE} = 15V, T_{VJ} = 125°C, R_G = 16Ω	I_{CM} = 20	A
(RBSOA)	Clamped inductive load	@ 0.8 • V_{CES}	
P_C	T_C = 25°C	110	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6mm (0.062 in.) from case for 10s	300	°C
T_{SOLD}	Plastic body for 10 seconds	260	°C
M_d	Mounting torque (TO-247)	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

Symbol	Test Conditions (T_J = 25°C unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250μA, V_{GE} = 0V	1700			V
$V_{GE(th)}$	I_C = 250μA, V_{CE} = V_{GE}	3.0		5.0	V
I_{CES}	V_{CE} = 0.8 • V_{CES}			50	μA
	V_{GE} = 0V T_J = 125°C			500	μA
I_{GES}	V_{CE} = 0V, V_{GE} = ± 20V			±100	nA
$V_{CE(sat)}$	I_C = I_{C90}, V_{GE} = 15V, Note 1		2.7	4.0	V
	T_J = 125°C		3.4		

Features

- International standard packages JEDEC TO-268 and JEDEC TO-247 AD
- High current handling capability
- MOS Gate turn-on
  - drive simplicity
- Rugged NPT structure
- Molding epoxies meet UL 94 V-0 flammability classification

Applications

- Capacitor discharge & pulser circuits
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

Advantages

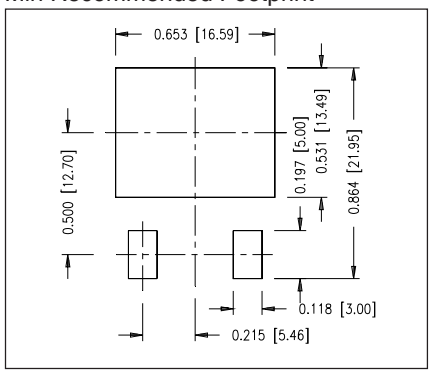
- High power density
- Suitable for surface mounting
- Easy to mount with 1 screw, (isolated mounting screw hole)

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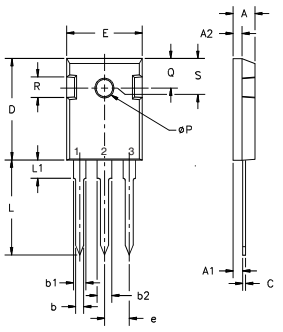
Symbol	Test Conditions (T_J = 25°C unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	I_C = 10A, V_{CE} = 10V, Note 1	3.8	6.3		S
$I_{C(ON)}$	V_{CE} = 10V, V_{GE} = 10V		33		A
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		700		pF
C_{oes}			40		pF
C_{res}			14		pF
Q_g	I_C = 10A, V_{GE} = 15V, V_{CE} = 0.5 • V_{CES}		32		nC
Q_{ge}			4		nC
Q_{gc}			16		nC
$t_{d(on)}$	**Resistive load, T_J = 25°C**		30		ns
t_r	I_C = 10A, V_{GE} = 15V		69		ns
$t_{d(off)}$	V_{CE} = 850V, R_G = 16Ω		132		ns
t_f			600		ns
$t_{d(on)}$	**Resistive load, T_J = 125°C**		30		ns
t_{ri}	I_C = 10A, V_{GE} = 15V		270		ns
$t_{d(off)}$	V_{CE} = 850V, R_G = 16Ω		135		ns
t_{fi}			495		ns
R_{thJC}				1.1	°C/W
R_{thCS}	(TO-247)		0.25		°C/W

Note 1: Pulse test, t ≤ 300µs, duty cycle, d ≤ 2%.

Min Recommended Footprint



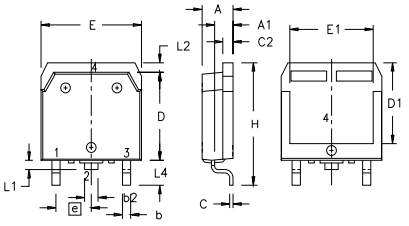
TO-247 AD Outline

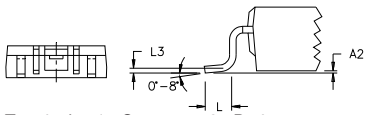


Terminals: 1 - Gate 2 - Drain

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216

TO-268 Outline





Terminals: 1 - Gate 2 - Drain

SYM	INCHES MIN	MAX	MILLIMETERS MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,850,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ 25ºC

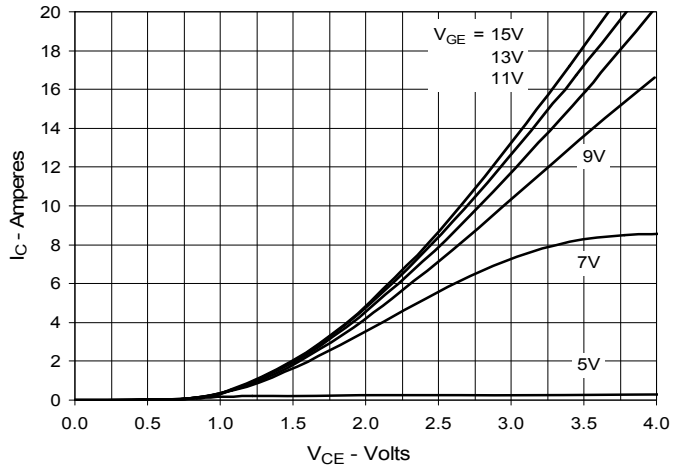


Fig. 2. Extended Output Characteristics @ 25ºC

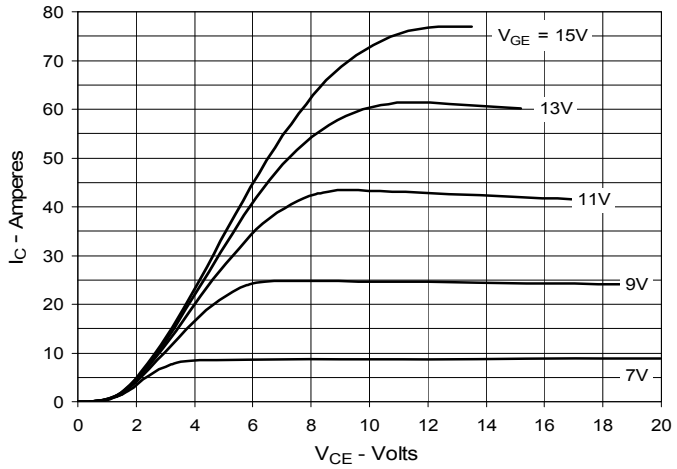


Fig. 3. Output Characteristics @ 125ºC

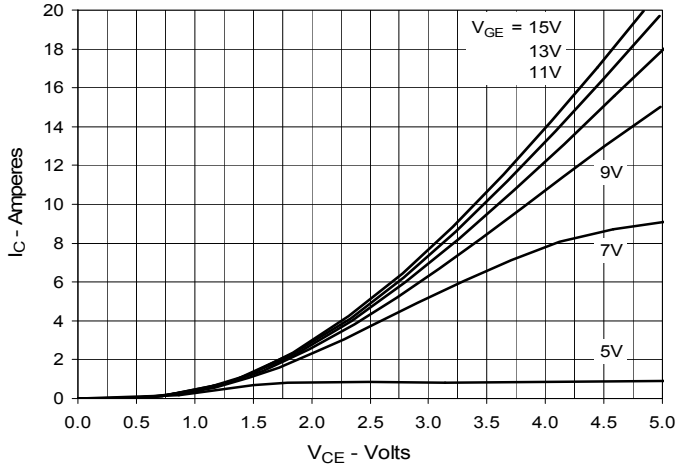


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

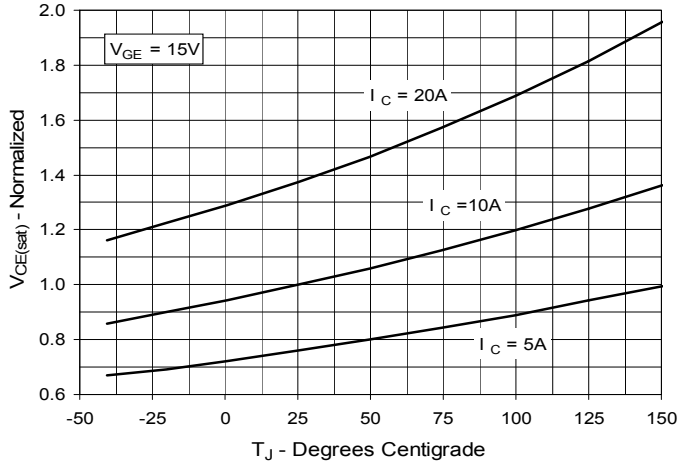


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

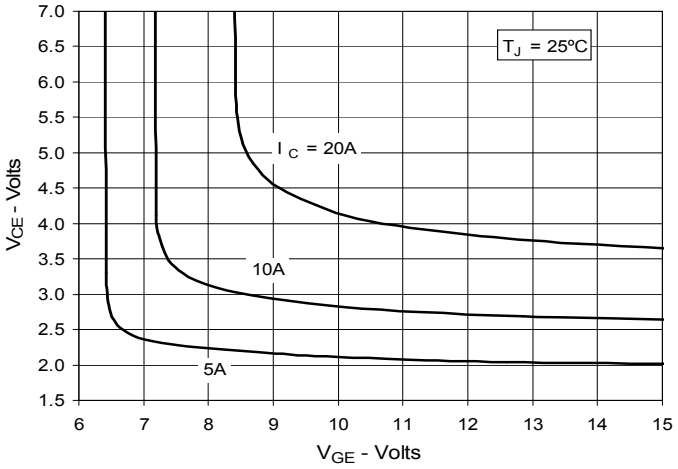
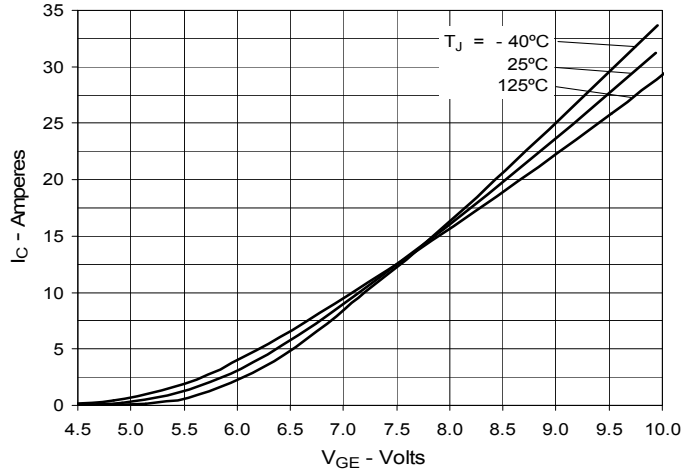


Fig. 6. Input Admittance



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Fig. 7. Transconductance

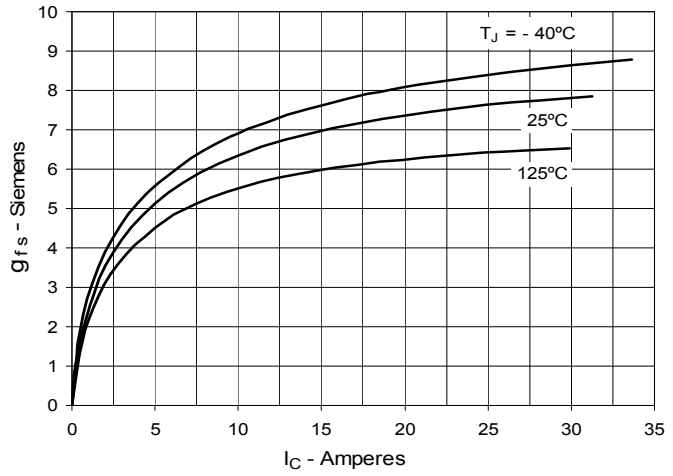


Fig. 8. Gate Charge

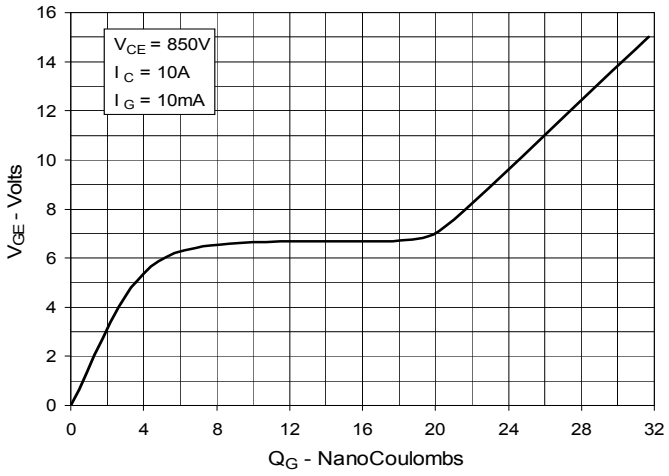


Fig. 9. Reverse-Bias Safe Operating Area

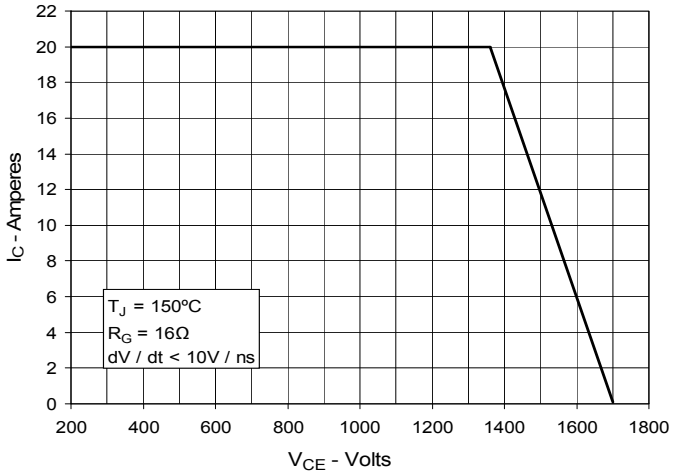


Fig. 10. Capacitance

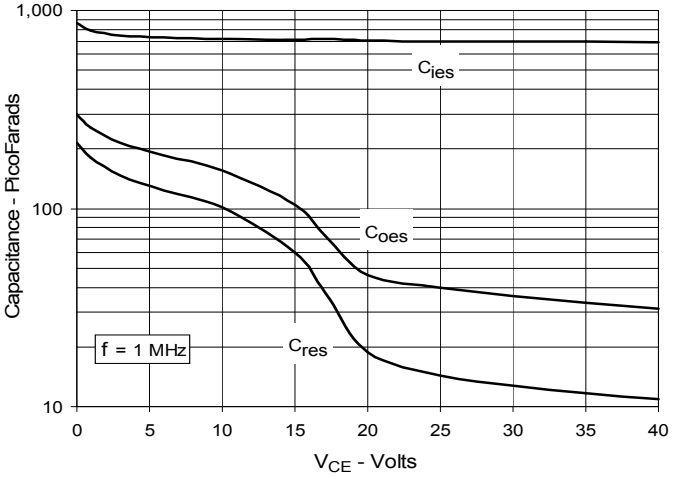
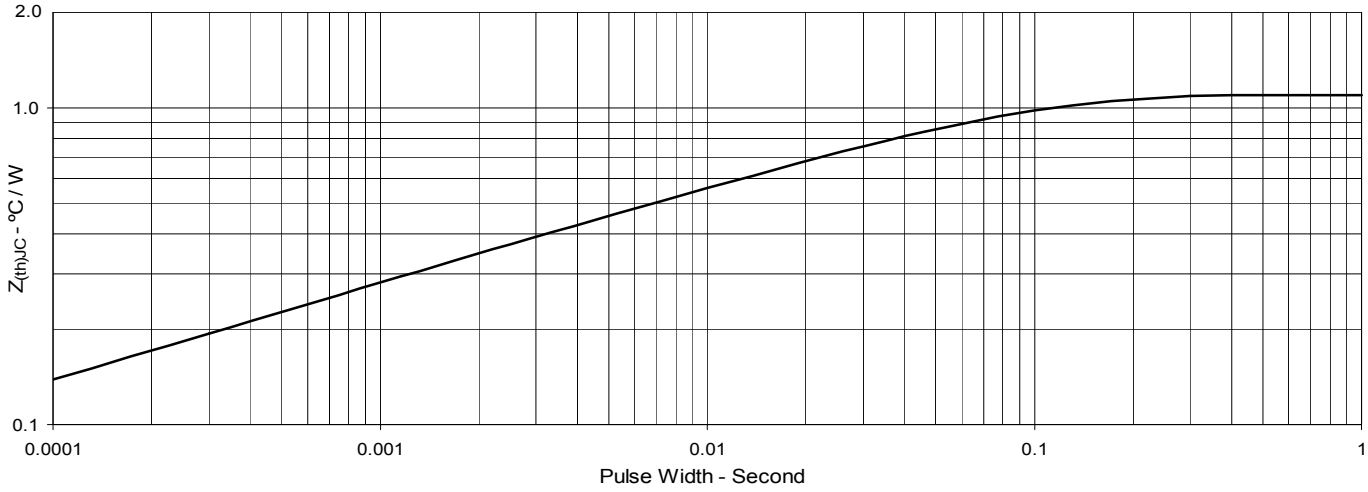


Fig. 11. Maximum Transient Thermal Impedance



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Fig. 12. Resistive Turn-on Rise Time vs. Junction Temperature

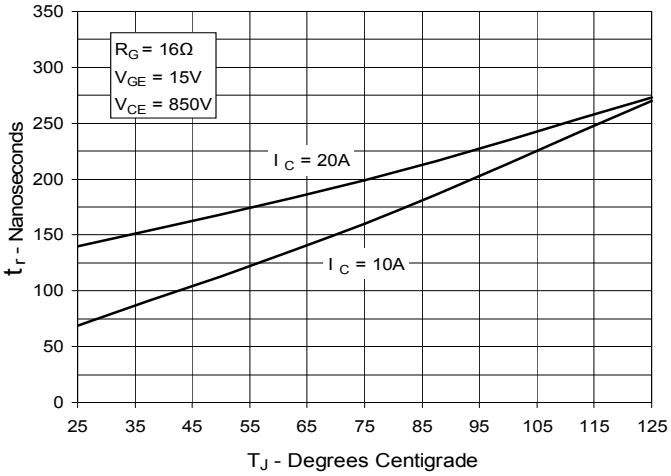


Fig. 13. Resistive Turn-on Rise Time vs. Collector Current

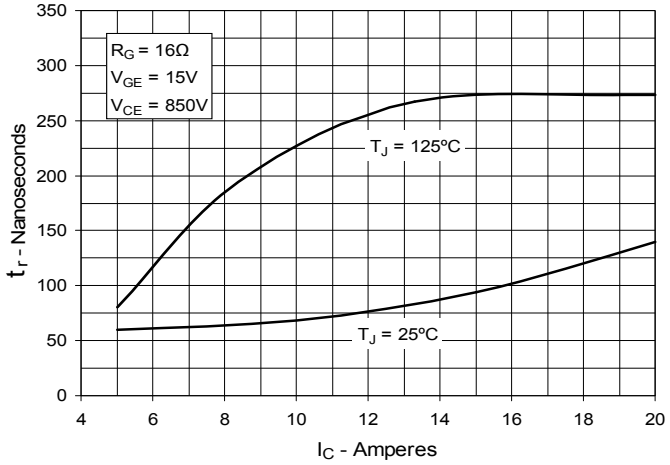


Fig. 14. Resistive Turn-on Switching Times vs. Gate Resistance

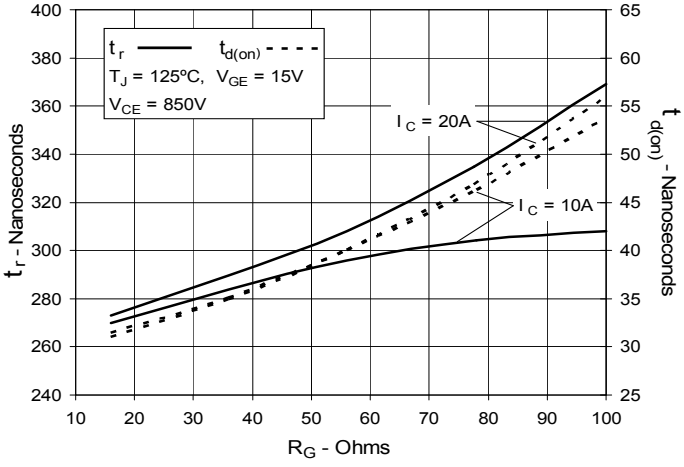


Fig. 15. Resistive Turn-off Switching Times vs. Junction Temperature

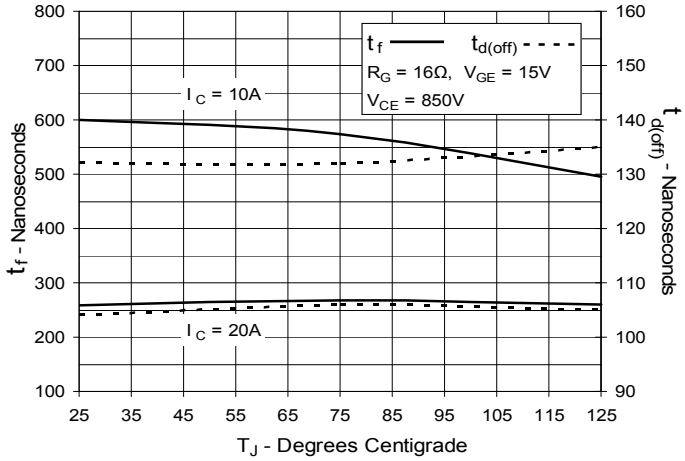


Fig. 16. Resistive Turn-off Switching Times vs. Collector Current

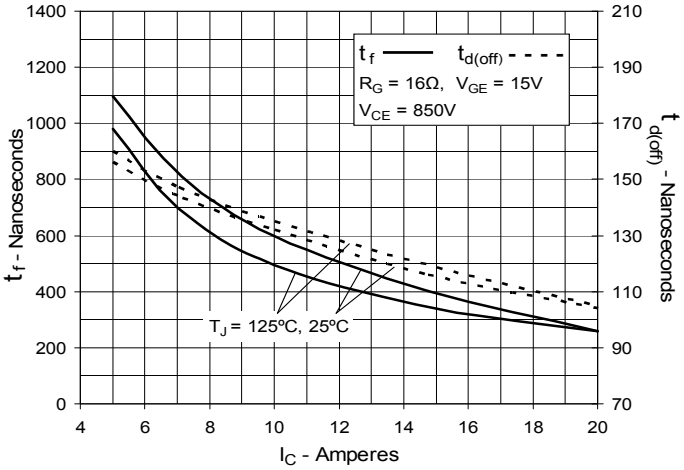
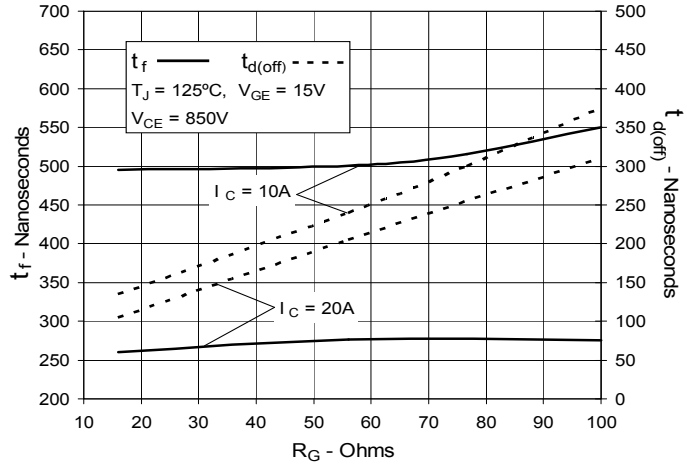


Fig. 17. Resistive Turn-off Switching Times vs. Gate Resistance



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